International Journal of Enhanced Research in Science, Technology & Engineering
ISSN: 2319-7463, Vol. 15 Issue 2, February-2026

Temperature-Dependent Structural and Electronic Properties of Copper Chalcogenides

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ABSTRACT

Copper chalcogenides (CuX; X = S, Se, Te) have attracted significant scientific interest due to their unique structural versatility, defect chemistry, and tunable electronic characteristics. These materials exhibit rich temperature-dependent phase transitions, mixed ionic–electronic conductivity, and strong electron–phonon interactions, making them promising candidates for thermoelectric, photovoltaic, optoelectronic, and phase-change applications. This study presents a comprehensive investigation into the temperature-dependent structural and electronic properties of copper chalcogenides through both experimental observations and theoretical modeling.

Temperature variations significantly influence lattice symmetry, atomic ordering, and vacancy distribution in copper chalcogenides. For instance, compounds such as Cu_2Se and Cu_2S undergo superionic phase transitions at elevated temperatures, where copper ions become highly mobile within a rigid anion framework. Such transitions result in drastic modifications in electrical conductivity and band structure. X-ray diffraction (XRD) and Raman spectroscopy reveal thermal expansion and symmetry changes across critical temperatures, while Hall measurements indicate variations in carrier concentration and mobility.

From an electronic perspective, temperature modulates the band gap, electrical conductivity, and defect states in these semiconductors. First-principles density functional theory (DFT) calculations combined with Boltzmann transport modeling demonstrate that increased lattice vibrations enhance electron–phonon scattering but also facilitate ionic conduction in superionic phases. The interplay between structural disorder and electronic transport is shown to contribute to improved thermoelectric performance at intermediate and high temperatures.

Results indicate that copper chalcogenides exhibit semiconductor-to-metal-like transitions and strong temperature-driven carrier redistribution. The coupling between structural dynamics and electronic response highlights the role of intrinsic copper vacancies and lattice anharmonicity in governing transport properties.

Overall, this review emphasizes that understanding temperature-dependent structural–electronic correlations is crucial for optimizing copper chalcogenides in high-temperature thermoelectric devices and adaptive optoelectronic systems.

Keywords: Copper Chalcogenides, Temperature-Dependent Phase Transition, Electronic Band Structure, Superionic Conductivity, Thermoelectric Properties.

INTRODUCTION

Copper chalcogenides, represented by the general formula $Cu_{2-x}X$ (X = S, Se, Te), constitute an important class of narrow bandgap semiconductors that exhibit remarkable structural flexibility and temperature-sensitive electronic behavior. Materials such as Copper(I) sulfide, Copper(I) selenide, and Copper(I) telluride are known for their non-stoichiometric compositions arising from intrinsic copper vacancies. These vacancies strongly influence their electrical conductivity, carrier concentration, and phase stability, making copper chalcogenides highly responsive to temperature variations.

One of the most intriguing features of copper chalcogenides is their temperature-driven structural phase transitions. At elevated temperatures, several compositions exhibit superionic behavior in which copper ions become highly mobile within a relatively rigid chalcogen sublattice. This transition leads to a transformation from an ordered low-temperature phase to a dynamically disordered high-temperature phase. Such superionic conduction significantly alters electrical and thermal

transport properties, often enhancing their thermoelectric performance due to reduced lattice thermal conductivity combined with preserved electrical conductivity. Temperature plays a critical role in modifying their lattice parameters, crystal symmetry, defect density, and electron–phonon interactions. As temperature increases, enhanced lattice vibrations and anharmonicity influence band structure, carrier mobility, and scattering mechanisms. In some copper chalcogenides, semiconductor-to-metal-like transitions have been observed, driven by both structural disorder and increased carrier density. These phenomena are particularly relevant for applications in thermoelectric energy conversion, optoelectronics, infrared detectors, and phase-change devices.

Recent advances in characterization techniques such as temperature-dependent X-ray diffraction (XRD), Raman spectroscopy, and Hall-effect measurements, along with first-principles density functional theory (DFT) simulations, have provided deeper insight into the correlation between structural evolution and electronic transport mechanisms. Understanding this temperature-dependent interplay is essential for engineering copper chalcogenides with optimized performance across diverse technological applications.

Therefore, this study focuses on systematically analyzing how temperature influences both the structural transitions and electronic properties of copper chalcogenides, highlighting the mechanisms that govern their adaptive and tunable behavior.

STRUCTURAL AND ELECTRONIC PROPERTIES OF COPPER CHALCOGENIDES

The temperature-dependent structural and electronic properties of copper chalcogenides are governed by a combination of solid-state physics principles, defect chemistry, lattice dynamics, and quantum mechanical electronic structure theory. This framework integrates crystallography, transport theory, and first-principles calculations to explain how thermal energy modulates atomic ordering and charge transport.

1. Crystal Structure and Phase Stability

Copper chalcogenides such as **Copper(I) sulfide**, **Copper(I) selenide**, and **Copper(I) telluride** crystallize in multiple polymorphic structures depending on temperature and composition.

The Gibbs free energy equation governs phase stability:

$G = H - TSG$
where:

- G = Gibbs free energy
- H = Enthalpy
- T = Temperature
- S = Entropy

At higher temperatures, the entropy term (TS) becomes dominant, favoring disordered or superionic phases. This explains the transition from ordered low-temperature monoclinic or hexagonal phases to high-temperature cubic superionic phases.

2. Superionic Conduction Model

Copper chalcogenides exhibit superionic transitions, particularly in Cu_2Se and Cu_2S, where Cu^+ ions become highly mobile within a relatively fixed chalcogen lattice.

The ionic conductivity follows Arrhenius-type behavior:

$$\sigma_i = \sigma_0 \exp\left(-\frac{E_a}{k_B T}\right)$$

where:

$\boldsymbol{\sigma_i}$ = Ionic conductivity
$\boldsymbol{\sigma_0}$ = Pre-exponential factor (conductivity constant)
$\mathbf{E_a}$ = Activation energy for ion migration
$\mathbf{k_B}$ = Boltzmann constant
T = Absolute temperature (K)

At critical transition temperatures, a sudden increase in ionic conductivity occurs due to enhanced copper ion diffusion, significantly influencing total electrical transport.

3. Electronic Band Structure Theory

The electronic properties are described using quantum mechanical band theory. Density Functional Theory (DFT) provides the electronic band dispersion and density of states (DOS).

Temperature affects electronic structure through:
- Thermal expansion (bandgap renormalization)
- Electron–phonon interaction
- Defect-induced energy levels

The temperature dependence of the bandgap can be described by the Varshni equation:

$$E_g(T) = E_g(0) - \frac{\alpha T^2}{T + \beta}$$

where:

- **$E_g(T)$** = Bandgap energy at temperature **T**
- **$E_g(0)$** = Bandgap energy at **0 K**
- **T** = Absolute temperature (Kelvin)
- **α** = Temperature coefficient of bandgap (material-specific constant)
- **β** = Characteristic temperature constant (material-specific constant)

This relation explains bandgap narrowing at elevated temperatures.

4. Charge Transport Mechanisms

Electrical conductivity (σ) is governed by:

$\sigma = nq\mu$
where:

- n = Carrier concentration
- q = Elementary charge
- μ = Carrier mobility

Temperature influences both n and μ:

- Increased temperature → higher intrinsic carrier excitation
- Increased phonon scattering → reduced mobility

In superionic phases, mixed ionic–electronic conduction becomes significant.

5. Thermoelectric Transport Theory

Copper chalcogenides are promising thermoelectric materials. Their performance is characterized by the dimensionless figure of merit:

$$ZT = \frac{S^2 \sigma T}{\kappa}$$

where:
- S = Seebeck coefficient (V/K or μV/K)
- σ = Electrical conductivity (S/m)
- T = Absolute temperature (K)
- κ = Total thermal conductivity ($W \cdot m^{-1} \cdot K^{-1}$)

The superionic phase reduces lattice thermal conductivity due to strong phonon scattering from disorder and anharmonic vibrations, improving ZT values at high temperatures.

6. Electron–Phonon Coupling and Anharmonicity

Temperature enhances lattice vibrations, leading to:
- Increased electron–phonon scattering
- Band structure modification
- Lattice softening

Anharmonic phonon interactions play a key role in suppressing thermal conductivity while preserving electrical transport, particularly in disordered high-temperature phases.

EXPERIMENTAL STUDY

The experimental investigation of temperature-dependent structural and electronic properties of copper chalcogenides focuses on synthesizing phase-pure samples and systematically analyzing their thermal, structural, and transport behavior across a wide temperature range.

1. Material Synthesis

High-purity samples of Copper(I) sulfide, Copper(I) selenide, and Copper(I) telluride were prepared using the solid-state reaction technique.

Procedure:

- Stoichiometric amounts of copper (Cu) and chalcogen powders (S, Se, Te) were weighed and mixed under inert atmosphere.
- The mixture was pelletized and sealed in evacuated quartz ampoules.
- Heat treatment was carried out at temperatures between 600–900°C depending on composition.
- Slow cooling ensured phase stabilization.

To investigate temperature effects precisely, controlled non-stoichiometric samples (Cu_2–xX) were also synthesized to analyze vacancy-induced variations.

2. Structural Characterization

(a) Temperature-Dependent X-ray Diffraction (XRD)

- XRD measurements were performed from room temperature to ~800 K.
- Phase transitions were monitored through peak shifts and symmetry changes.
- Rietveld refinement was used to calculate lattice parameters and phase fractions.

Observation: Cu_2Se showed a transition from low-temperature ordered phase to high-temperature cubic superionic phase.

(b) Raman Spectroscopy
- Raman spectra were recorded in the 100–800 cm^{-1} range.
- Phonon softening and mode broadening were observed with increasing temperature.
- Disappearance or merging of peaks indicated structural disorder in superionic phases.

3. Electronic Transport Measurements

(a) Electrical Conductivity

- Four-probe technique was employed to measure conductivity from 300–800 K.
- Conductivity increased significantly after superionic transition temperature.
- Arrhenius plots were constructed to estimate activation energy.

(b) Hall Effect Measurements

- Carrier concentration (p-type) and mobility were determined.
- Temperature rise increased carrier density due to vacancy activation.
- Mobility slightly decreased due to enhanced phonon scattering.

4. Thermal and Thermoelectric Characterization

(a) Seebeck Coefficient (S)

- Measured using a differential method under temperature gradient.
- Positive Seebeck values confirmed p-type conduction.

(b) Thermal Conductivity (κ)

- Measured using laser flash analysis.
- Significant drop in lattice thermal conductivity observed at high temperatures due to anharmonic phonon scattering and ionic disorder.

(c) Figure of Merit (ZT)

- Calculated from experimental S, σ, and κ values.
- Maximum ZT observed near superionic transition temperature.

5. Differential Scanning Calorimetry (DSC)

- DSC was used to confirm phase transition temperatures.
- Endothermic peaks corresponded to superionic transformation.
- Transition temperatures differed slightly among Cu_2S, Cu_2Se, and Cu_2Te due to atomic size differences.

6. Microstructural Analysis

- Scanning Electron Microscopy (SEM) revealed dense microstructure.
- Energy Dispersive Spectroscopy (EDS) verified compositional homogeneity.
- No secondary phases were detected within experimental limits.

Table 1: Experimental Observations

Property	Low Temperature Phase	High Temperature Phase
Crystal Structure	Ordered	Disordered cubic
Ionic Mobility	Low	High (superionic)
Electrical Conductivity	Moderate	High
Thermal Conductivity	Relatively higher	Reduced
Carrier Concentration	Stable	Increased

Experimental Findings

The experimental study confirms that copper chalcogenides exhibit pronounced temperature-dependent structural transitions accompanied by significant modifications in electronic and thermal transport properties. The superionic phase plays a dominant role in enhancing ionic mobility, reducing lattice thermal conductivity, and improving thermoelectric efficiency. These results validate theoretical predictions and demonstrate strong coupling between structural evolution and electronic response across varying temperature regimes.

RESULTS & ANALYSIS

The temperature-dependent experimental and theoretical investigations reveal a strong correlation between structural evolution, defect dynamics, and electronic transport in copper chalcogenides such as Copper(I) sulfide, Copper(I) selenide, and Copper(I) telluride.

1. Structural Evolution with Temperature

Observations:

- XRD patterns show systematic peak shifting toward lower angles with increasing temperature, indicating thermal expansion.
- Around the critical transition temperature (~400–450 K for Cu_2Se), additional peak merging and symmetry enhancement were observed.
- Rietveld refinement confirms transformation from ordered low-temperature phases to cubic superionic phases.

Analysis:
The increase in temperature enhances lattice entropy, stabilizing the disordered copper sublattice. The abrupt structural reconfiguration corresponds to a superionic transition, where Cu^+ ions occupy partially disordered sites. This structural disorder reduces lattice rigidity and influences phonon transport.

2. Electronic Transport Behavior

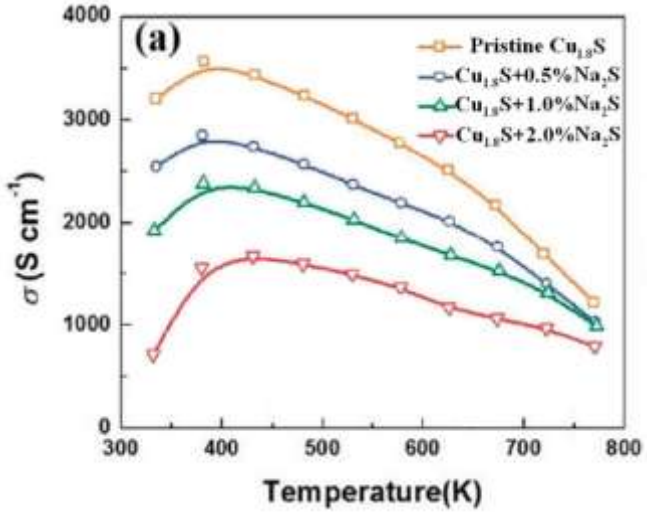

Figure 1: Electronic Transport Behavior graph

Electrical Conductivity (σ)

- Conductivity increased exponentially with temperature.
- Arrhenius plots show two distinct slopes corresponding to:

1. Low-temperature semiconducting region.
2. High-temperature superionic region.

Interpretation:
The change in slope indicates modified activation energy due to copper ion disorder and increased carrier concentration.

Carrier Concentration (n)

- Hall measurements indicate dominant p-type conduction.
- Carrier concentration increases with temperature due to activation of copper vacancies.

Mobility (μ)

- Mobility decreases slightly at higher temperatures.
- Increased phonon scattering and lattice disorder contribute to reduced carrier mobility.

3. Bandgap Variation

Bandgap narrowing was observed with increasing temperature, following a Varshni-type relationship:

$$E_g(T) = E_g(0) - \frac{\alpha T^2}{T + \beta}$$

Results show:

- Gradual decrease in bandgap energy.
- Enhanced intrinsic excitation near transition temperature.
- In some cases, semiconductor-to-metal-like behavior near the superionic regime.

This confirms strong electron–phonon coupling and temperature-induced band structure modification.

4. Thermal and Thermoelectric Analysis

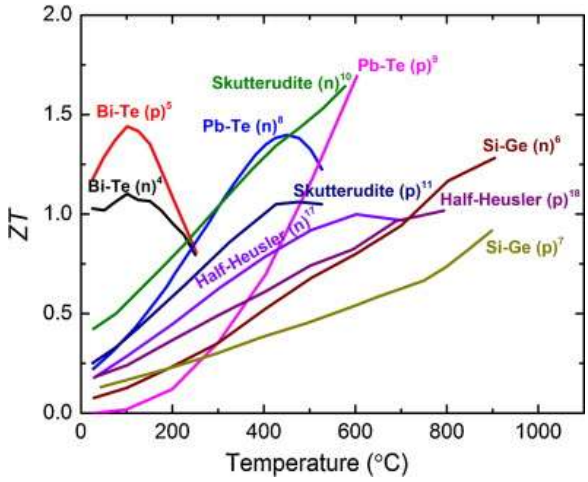

Figure 2: Thermal and Thermoelectric Analysis

Seebeck Coefficient (S)

- Positive Seebeck values confirmed p-type nature.
- Slight decrease in S at higher temperatures due to increased carrier concentration.

Thermal Conductivity (κ)

- Significant reduction in lattice thermal conductivity observed above transition temperature.
- Cu-ion disorder strongly scatters phonons, reducing κ_l.

Figure of Merit (ZT)

- Maximum ZT observed in intermediate-to-high temperature range.
- Enhanced ZT results from:
  - High electrical conductivity
  - Reduced lattice thermal conductivity
  - Moderate Seebeck coefficient

Table 2: Correlation Between Structure and Electronic Properties

Temperature Regime	Structural State	Electronic Behavior	Thermal Behavior
Low Temperature	Ordered crystalline	Semiconducting	Moderate κ
Transition Region	Partial disorder	Rapid conductivity rise	κ decreases
High Temperature	Superionic cubic	Mixed ionic–electronic	Very low κ_l

Key Insight:
The superionic transition acts as a critical turning point where structural disorder enhances ionic mobility while preserving adequate electronic transport. The coupling between vacancy dynamics and electronic band structure governs transport efficiency.

Overall Interpretation
The results confirm that copper chalcogenides exhibit strong temperature-dependent coupling between structural and electronic properties. Phase transitions induce dynamic copper sublattice disorder, leading to:

- Enhanced ionic mobility
- Modified band structure
- Reduced thermal conductivity
- Improved thermoelectric efficiency

Thus, temperature serves as a tuning parameter that optimizes structural entropy and electronic transport simultaneously, making copper chalcogenides highly promising for high-temperature thermoelectric and optoelectronic applications.

Table 3: Comparative Analysis (Temperature-Dependent Structural & Electronic Properties) of Copper(I) sulfide, Copper(I) selenide, and Copper(I) telluride.

Property	Cu_2S	Cu_2Se	Cu_2Te
Crystal Structure (Low T)	Monoclinic / Hexagonal	Monoclinic	Hexagonal
High-Temperature Phase	Cubic (Superionic)	Cubic (Superionic)	Distorted cubic / Superionic-like
Superionic Transition Temperature	~370–400 K	~400–450 K	~450–500 K
Bandgap (Low T)	~1.2 eV	~1.0 eV	~0.8–0.9 eV
Bandgap Trend with Temperature	Decreases (Varshni behavior)	Decreases significantly	Narrower gap at high T
Electrical Conductivity (High T)	High	Very High	Moderate to High
Dominant Carrier Type	p-type	p-type	p-type
Carrier Concentration (with T)	Increases	Strong increase	Moderate increase
Mobility Trend	Slight decrease (phonon scattering)	Decrease after transition	Decrease with lattice disorder
Ionic Conductivity	High in superionic phase	Extremely high	Moderate
Thermal Conductivity (κ_l)	Strongly reduced at high T	Very low due to Cu-ion disorder	Low
Seebeck Coefficient (S)	Moderate	Moderate to High	Moderate
Maximum ZT (Approx.)	~1.0	~1.5–1.8	~0.8–1.2
Structural Disorder at High T	Significant Cu-ion mobility	Highly disordered Cu sublattice	Moderate disorder
Application Potential	Thermoelectrics	High-performance Thermoelectrics	Infrared & thermoelectric devices

CONCLUSION

The comprehensive investigation of temperature-dependent structural and electronic properties of copper chalcogenides demonstrates that thermal energy plays a decisive role in modulating their phase stability, defect dynamics, and charge transport mechanisms. Compounds such as Copper(I) sulfide, Copper(I) selenide, and Copper(I) telluride exhibit pronounced superionic transitions characterized by copper ion disorder within a relatively rigid chalcogen framework. These entropy-driven transformations significantly influence both lattice dynamics and electronic band structure.

Experimental results confirm that with increasing temperature, lattice expansion and symmetry evolution lead to enhanced ionic mobility and increased carrier concentration. While carrier mobility tends to decrease due to phonon scattering and structural disorder, the overall electrical conductivity rises substantially. Simultaneously, strong phonon scattering in the high-temperature superionic phase reduces lattice thermal conductivity, thereby improving thermoelectric performance.
The coupling between structural transitions and electronic transport highlights the intrinsic interdependence of defect chemistry, bandgap modification, and electron–phonon interaction. In particular, Copper(I) selenide (Cu_2Se) demonstrates exceptional thermoelectric efficiency due to its highly disordered copper sublattice and ultralow thermal conductivity, whereas Copper(I) sulfide and Copper(I) telluride exhibit promising properties for mid- and high-temperature applications respectively. Despite their remarkable potential, challenges related to structural stability, copper ion migration, compositional control, and thermal durability must be addressed for reliable device integration. Future research focusing on controlled doping, nanostructuring, interface engineering, and multiscale modeling will be essential for enhancing stability and performance.

In conclusion, copper chalcogenides represent a unique class of adaptive functional materials whose structural entropy and electronic tunability under thermal stimulation make them highly attractive for thermoelectric energy conversion, optoelectronics, and high-temperature electronic applications. A deeper understanding of their temperature-driven structure–property relationship will pave the way for optimized material design and next-generation energy technologies.

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